



E. Compound Semiconductors 분과

2021년 1월 27일(수), 10:45-12:15 / 채널 C

[WC2-E] Compound Semiconductors II

좌장: 권혁인 교수 (중앙대학교)

<p>WC2-E-1 10:45-11:00</p>	<p>High Performance Flexible InAs Photodetectors for Advanced Imaging System Seungwan Woo^{1,3}, Geunhwan Ryu¹, Soo Seok Kang, Namgi Hong¹, Rafael Jumar Chu^{1,2}, In-Hwan Lee³, Daehwan Jung^{1,2}, and Won Jun Choi¹ ¹Center for Opto-electronic Materials and Devices, KIST, ²Division of Nano and Information Technology, KIST School at University of Science and Technology, ³Department of Materials Science and Engineering, Korea University</p>
<p>WC2-E-2 11:00-11:15</p>	<p>Lasing Characteristic of Quantum Dot Laser Diode Transferred onto Silicon via Epitaxial Lift-Off Jae-Hoon Han¹, Daehwan Jung^{1,2}, GeunHwan Ryu¹, Jin-Dong Song^{1,2}, and Won Jun Choi¹ ¹Center for Opto-Electronic Materials and Devices, KIST, ²UST</p>
<p>WC2-E-3 11:15-11:30</p>	<p>Investigation of Proton Effects on AlGaIn/GaN HEMTs with Various Buffer Structure Eunjin Kim¹, Jeong-Gil Kim¹, Seung-Hyeon Kang¹, Dong-Seok Kim², and Jung-Hee Lee¹ ¹School of Electronic and Electrical Engineering, Kyungpook National University, ²KAERI</p>
<p>WC2-E-4 11:30-11:45</p>	<p>Opto-electrical Characteristics of Wafer-bonded InGaAs PhotoFET on Si Soo Seok Kang, Dae-Hwan Ahn, Jindong Song, and Jae-Hoon Han Center for Opto-Electronic Materials and Devices, KIST</p>
<p>WC2-E-5 11:45-12:00</p>	<p>Vertical Homo-Junction In_{0.53}Ga_{0.47}As TFETs With S_{min} = 52 mV/decade Ji-Min Baek¹, Tae-Woo Kim², and Dae-Hyun Kim¹ ¹School of Electronic and Electrical Engineering, Kyungpook National University, ²University of Ulsan</p>
<p>WC2-E-6 12:00-12:15</p>	<p>Analytical 채널 Charge Model of In_{0.7}Ga_{0.3}As Quantum-Well Heterostructure-FETs from Subthreshold to Inversion Hyeon-Seok Jeong, Hyun-Jeong Jung, Wan-Soo Park, Hyeon-Bhin Jo, In-Guen Lee, and Dae-Hyun Kim School of Electronics Engineering, Kyungpook National University</p>

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